

Features

- High density cell design for ultra low $R_{DS(on)}$
- Fully characterized avalanche voltage and current
- Good stability and uniformity with high E_{AS}
- Excellent package for good heat dissipation

Application

- Load switching
- Hard switched and high frequency circuits
- Uninterruptible power supply



MU0C80A: Device code
 XXXX : Code

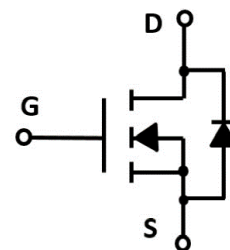
Marking and pin assignment

Product Summary

V_{DS}	$R_{DS(ON)}$ TYP	I_D
20V	4.0mΩ@4.5V	80A
	4.7mΩ@2.5V	



TO-252 top view



Schematic diagram



Pb-Free



Halogen-Free

Absolute Maximum Ratings (TA=25°C unless otherwise noted)

Symbol	Parameter	Rating	Unit
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Common Ratings (TC=25°C Unless Otherwise Noted)

V_{DS}	Drain-Source Breakdown Voltage	20	V
V_{GS}	Gate-Source Voltage	±12	V
T_J	Maximum Junction Temperature	150	°C
T_{STG}	Storage Temperature Range	-50 to 155	°C
I_S	Diode Continuous Forward Current	$T_C=25^\circ\text{C}$ 80	A

Mounted on Large Heat Sink

I_{DM}	Pulse Drain Current Tested	$T_C=25^\circ\text{C}$ 210	A
I_D	Continuous Drain Current	$T_C=25^\circ\text{C}$ 80	A
P_D	Maximum Power Dissipation	$T_C=25^\circ\text{C}$ 60	W
E_{AS}	Single pulse avalanche energy	200	mJ

Ordering Information (Example)

Type	Package	Marking	Minimum Package(pcs)	Inner Box Quantity(pcs)	Outer Carton Quantity(pcs)	Delivery Mode
MU0C80A	TO-252	MU0C80A	2,500	5,000	35,000	13"reel

Electrical Characteristics (T_J=25 °C unless otherwise noted)

Symbol	Parameter	Condition	Min	Typ	Max	Unit
Static Electrical Characteristics @ TJ = 25°C (unless otherwise stated)						
BV _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250μA	20	--	--	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =20V, V _{GS} =0V	--	--	1	μA
I _{GSS}	Gate-Body Leakage Current	V _{GS} =±12V, V _{DS} =0V	--	--	±100	nA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250μA	0.45	0.75	1.2	V
R _{DS(on)}	Drain-Source On-State Resistance	V _{GS} =4.5V, I _D =20A	--	4.0	5.0	mΩ
		V _{GS} =2.5V, I _D =15A	--	4.7	6.2	mΩ
Dynamic Electrical Characteristics @ TJ = 25°C (unless otherwise stated)						
C _{ISS}	Input Capacitance	V _{DS} =10V, V _{GS} =0V, f=1MHz	--	2000	--	pF
C _{OSS}	Output Capacitance		--	500	--	pF
C _{RSS}	Reverse Transfer Capacitance		--	200	--	pF
Switching Characteristics						
Q _g	Total Gate Charge	V _{DS} =10V, I _D =20A, V _{GS} =10V	--	25	--	nC
Q _{gs}	Gate Source Charge		--	6.6	--	nC
Q _{gd}	Gate Drain Charge		--	6.3	--	nC
t _{d(on)}	Turn-on Delay Time	V _{DD} =10V, I _D =20A, V _{GS} =4.5V, R _G =3Ω	--	6.5	--	nS
t _r	Turn-on Rise Time		--	17	--	nS
t _{d(off)}	Turn-Off Delay Time		--	30	--	nS
t _f	Turn-Off Fall Time		--	15.5	--	nS
Source- Drain Diode Characteristics						
V _{SD}	Forward on voltage	T _J =25°C, I _S =20A	--	--	1.2	V

Typical Operating Characteristics

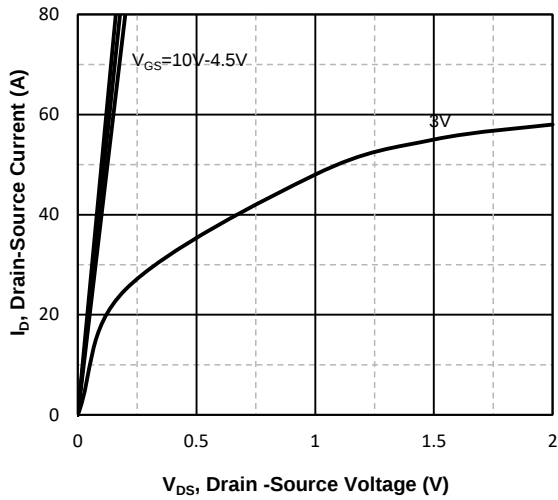


Fig1. Typical Output Characteristics

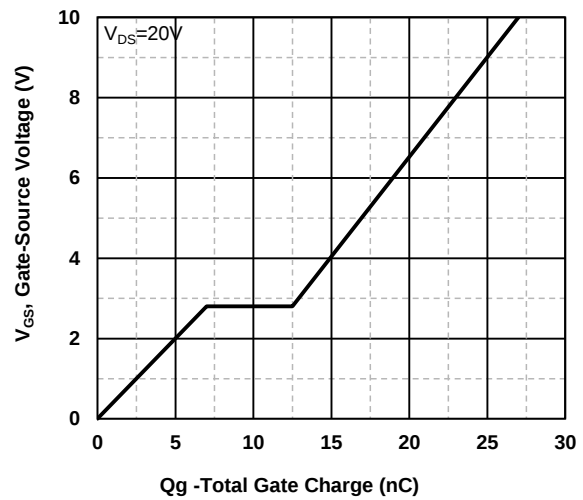


Fig2. Typical Gate Charge Vs. Gate-Source Voltage

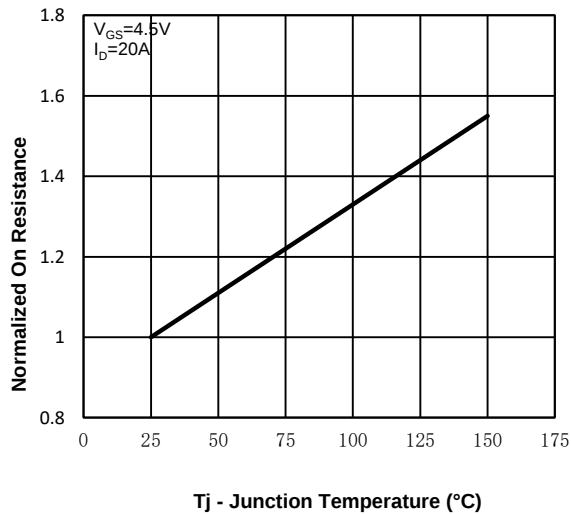


Fig3. Normalized On-Resistance Vs. Temperature

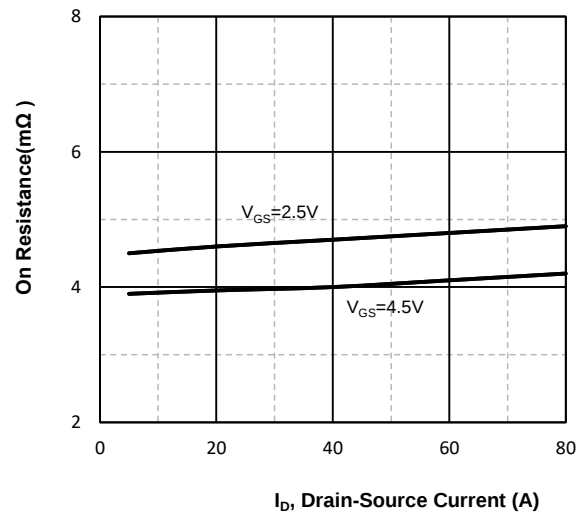


Fig4. On-Resistance Vs. Drain-Source Current

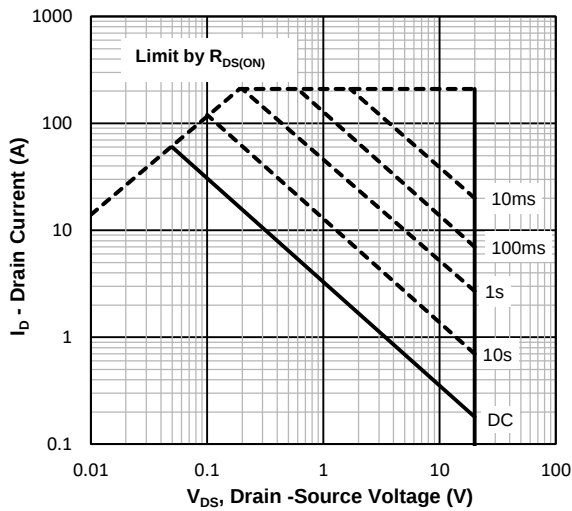


Fig5. Maximum Safe Operating Area

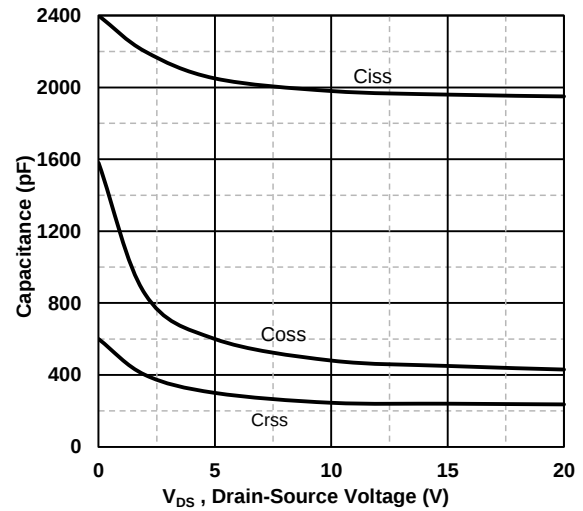
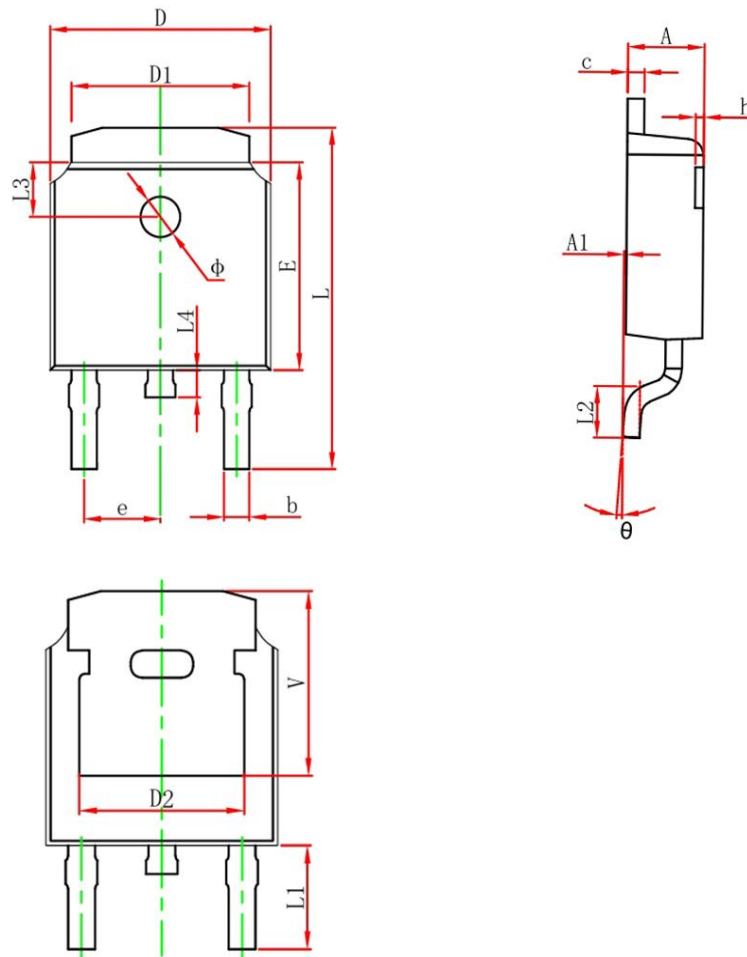


Fig6 Typical Capacitance Vs. Drain-Source Voltage

TO-252 Package information



Symbol	Dimensions in Millimeters(mm)		Dimensions In Inches	
	Min	Max	Min	Max
A	2.200	2.400	0.087	0.094
A1	0.000	0.127	0.000	0.005
b	0.635	0.770	0.025	0.030
c	0.450	0.580	0.018	0.023
D	6.500	6.700	0.256	0.264
D1	5.100	5.460	0.201	0.215
D2	4.830 REF.		0.190 REF.	
E	6.000	6.200	0.236	0.244
e	2.186	2.386	0.086	0.094
L	9.712	10.312	0.386	0.406
L1	2.900 REF.		0.114 REF.	
L2	1.400	1.700	0.055	0.067
L3	1.600 REF.		0.063 REF.	
L4	0.600	1.000	0.024	0.039
Φ	1.100	1.300	0.043	0.051
θ	0°	8°	0°	8°
h	0.000	0.300	0.000	0.012
V	5.250 REF.		0.207 REF.	